Supplementary Information

Cu₂ZnSnS₄ Thin Films: Spin Coating Synthesis and Photoelectrochemistry

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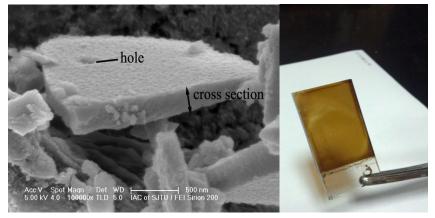


Fig. S1 Cross-sectional SEM image and optical picture of the CZTS thin film. The thicknesses of the sample is 300-400 nm. The observed chip is the one flipped off from FTO substrate.

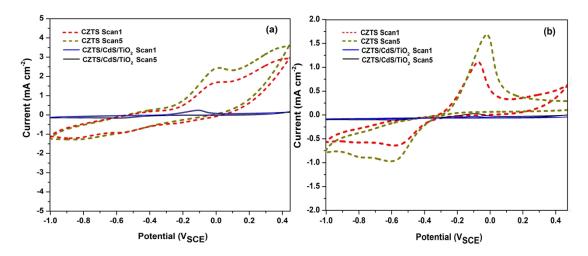


Fig. S2 Cyclic voltammograms under dark (a) and light (b) conditions of the bared and protected CZTS thin films in a conventional three electrode configuration. Scan1, scan one time; Scan 5, scan 5 times repeatedly. The potential was swept at 0.05 V s⁻¹ toward negative potential. Electrolyte, 0.2 mol L⁻¹ Na₂SO₄ aqueous solution; reference electrode, SCE; counter electrode, Pt wire.



Fig. S3 Optical images of unprotected (left) and CdS/TiO₂ coated (right) samples after cyclic voltammograms.